

Improved Quad CMOS Analog Switches

FEATURES

- ± 22 -V Supply Voltage Rating
- TTL and CMOS Compatible Logic
- Low On-Resistance— $r_{DS(on)}$: 50 Ω
- Low Leakage— $I_{D(on)}$: 20 pA
- Single Supply Operation Possible
- Extended Temperature Range
- Fast Switching— t_{ON} : 120 ns
- Low Charge Injection— Q : 1 pC

BENEFITS

- Wide Analog Signal Range
- Simple Logic Interface
- Higher Accuracy
- Minimum Transients
- Reduced Power Consumption
- Superior to DG211/212
- Space Savings (TSSOP)

APPLICATIONS

- Industrial Instrumentation
- Test Equipment
- Communications Systems
- Disk Drives
- Computer Peripherals
- Portable Instruments
- Sample-and-Hold Circuits

DESCRIPTION

The DG211B/212B analog switches are highly improved versions of the industry-standard DG211/212. These devices are fabricated in Vishay Siliconix' proprietary silicon gate CMOS process, resulting in lower on-resistance, lower leakage, higher speed, and lower power consumption.

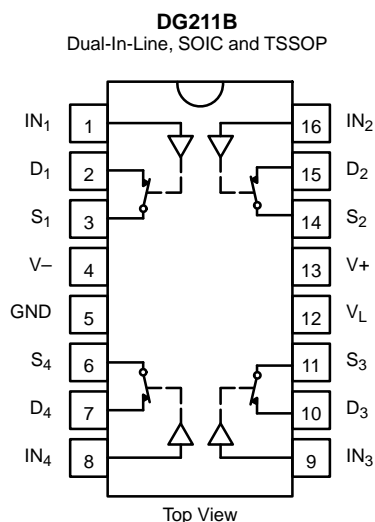
These quad single-pole single-throw switches are designed for a wide variety of applications in telecommunications, instrumentation, process control, computer peripherals, etc. An improved charge injection compensation design minimizes switching transients. The DG211B and DG212B can handle

up to ± 22 V, and have an improved continuous current rating of 30 mA. An epitaxial layer prevents latchup.

All devices feature true bi-directional performance in the on condition, and will block signals to the supply levels in the off condition.

The DG211B is a normally closed switch and the DG212B is a normally open switch. (See Truth Table.)

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE		
Logic	DG211B	DG212B
0	ON	OFF
1	OFF	ON

Logic "0" ≤ 0.8 V
Logic "1" ≥ 2.4 V

ORDERING INFORMATION		
Temp Range	Package	Part Number
-40 to 85 °C	16-Pin Plastic DIP	DG211BDJ
		DG212BDJ
	16-Pin Narrow SOIC	DG211BDY
		DG212BDY
	16-Pin TSSOP	DG211BDQ
		DG212BDQ

ABSOLUTE MAXIMUM RATINGS

Voltages Referenced to V-

V+ 44 V

GND 25 V

Digital Inputs^a V_S, V_D (V-) -2 V to (V+) +2 V
or 30 mA, whichever occurs first

Current, Any Terminal 30 mA

Peak Current, S or D

(Pulsed at 1 ms, 10% duty cycle max) 100 mA

Storage Temperature -65 to 125 °C

Power Dissipation (Package)^b

16-Pin Plastic DIP^c 470 mW

16-Pin Narrow SOIC and TSSOP^d 640 mW

Notes:

- Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- All leads welded or soldered to PC Board.
- Derate 6.5 mW/°C above 75 °C
- Derate 7.6 mW/°C above 75 °C

SCHEMATIC DIAGRAM (TYPICAL CHANNEL)

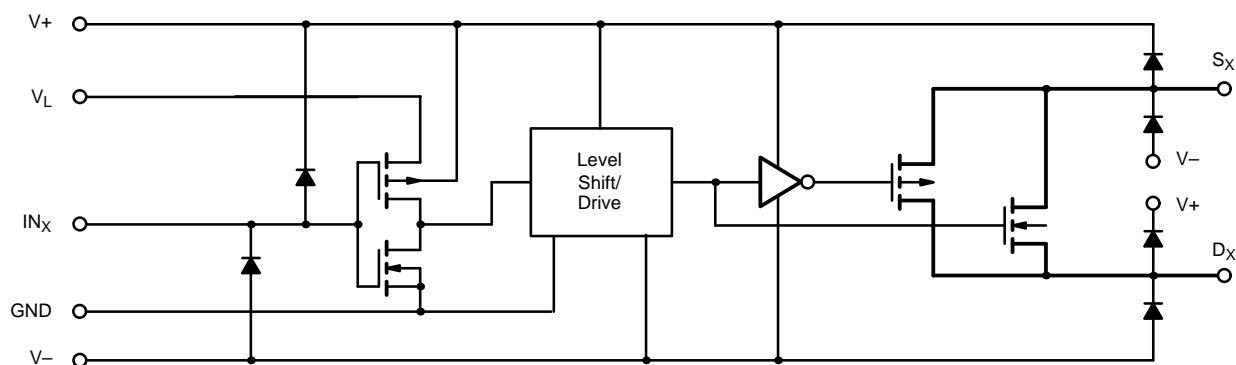


FIGURE 1.



SPECIFICATIONS							
Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15\text{ V}, V_- = -15\text{ V}$ $V_L = 5\text{ V}, V_{IN} = 2.4\text{ V}, 0.8\text{ V}^e$	Temp ^a	D Suffix -40 to 85°C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V_{ANALOG}		Full	-15		15	V
Drain-Source On-Resistance	$r_{DS(on)}$	$V_D = \pm 10\text{ V}, I_S = 1\text{ mA}$	Room		45	85	Ω
$r_{DS(on)}$ Match	$\Delta r_{DS(on)}$		Full		2	100	
Source Off Leakage Current	$I_{S(off)}$	$V_S = \pm 14\text{ V}, V_D = \mp 14\text{ V}$	Room	-0.5	± 0.01	0.5	nA
Drain Off Leakage Current	$I_{D(off)}$	$V_D = \pm 14\text{ V}, V_S = \mp 14\text{ V}$	Full	-5	± 0.01	5	
Drain On Leakage Current	$I_{D(on)}$	$V_S = V_D = \pm 14\text{ V}$	Room	-0.5	± 0.02	0.5	
			Full	-10		10	
Digital Control							
Input Voltage High	V_{INH}		Full	2.4			V
Input Voltage Low	V_{INL}		Full			0.8	
Input Current	I_{INH} or I_{INL}	V_{INH} or V_{INL}	Full	-1		1	μA
Input Capacitance	C_{IN}		Room		5		pF
Dynamic Characteristics							
Turn-On Time	t_{ON}	$V_S = 10\text{ V}$ See Figure 2	Room			300	ns
Turn-Off Time	t_{OFF}		Room			200	
Charge Injection	Q	$C_L = 1000\text{ pF}, V_g = 0\text{ V}, R_g = 0\ \Omega$	Room		1		pC
Source-Off Capacitance	$C_{S(off)}$	$V_S = 0\text{ V}, f = 1\text{ MHz}$	Room		5		pF
Drain-Off Capacitance	$C_{D(off)}$		Room		5		
Channel On Capacitance	$C_{D(on)}$	$V_D = V_S = 0\text{ V}, f = 1\text{ MHz}$	Room		16		
Off Isolation	OIRR	$C_L = 15\text{ pF}, R_L = 50\ \Omega$ $V_S = 1\text{ V}_{RMS}, f = 100\text{ kHz}$	Room		90		dB
Channel-to-Channel Crosstalk	X_{TALK}		Room		95		
Power Supply							
Positive Supply Current	I_+	$V_{IN} = 0\text{ or }5\text{ V}$	Room			10	μA
Negative Supply Current	I_-		Full			50	
Logic Supply Current	I_L	Room				10	
Power Supply Range for Continuous Operation	V_{OP}		Full	± 4.5		± 22	V

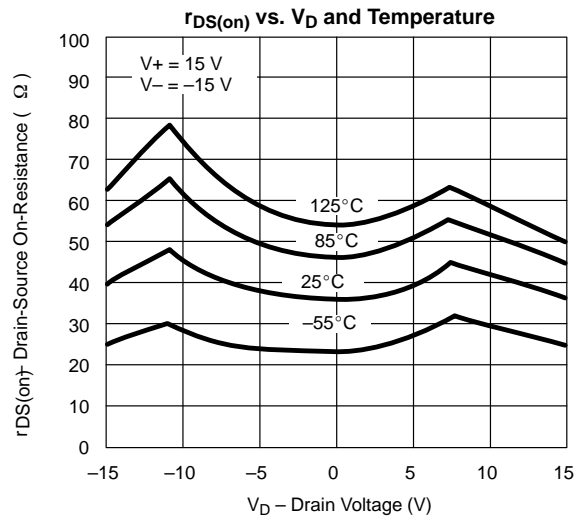
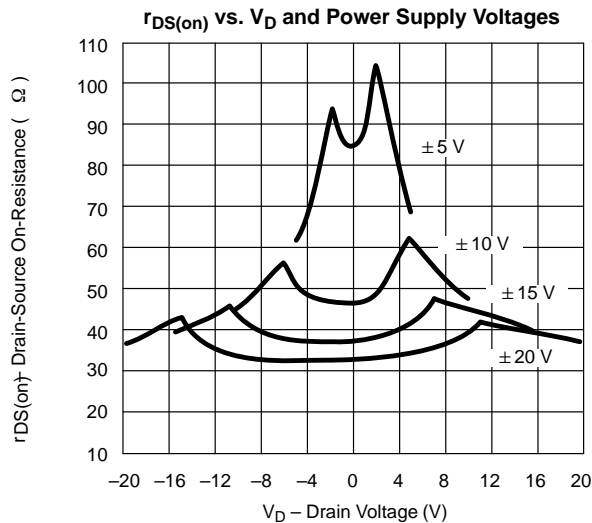


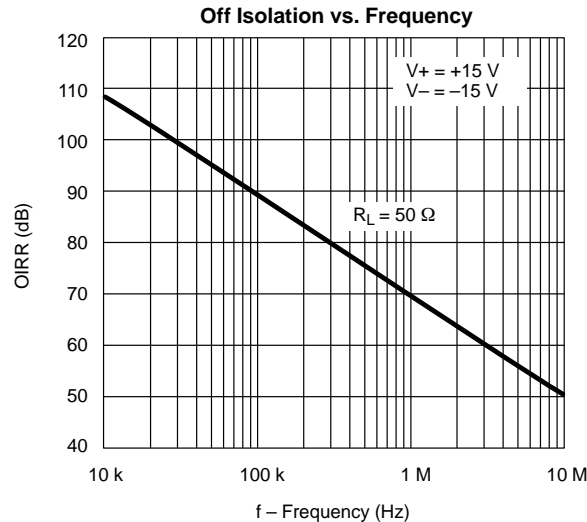
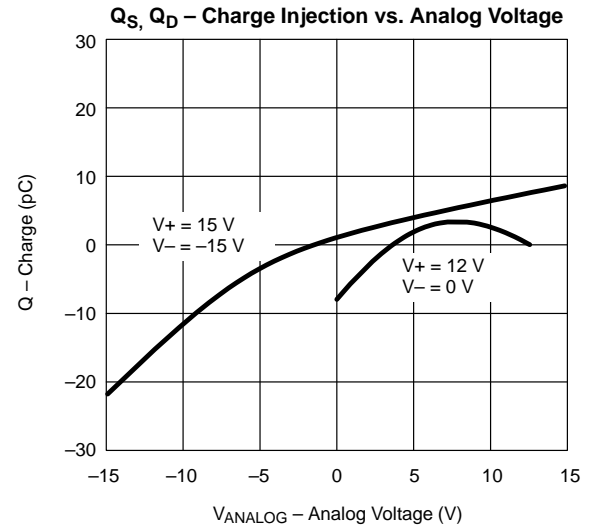
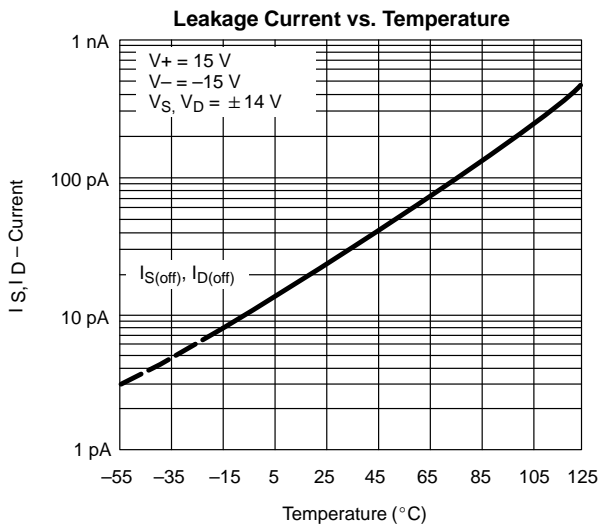
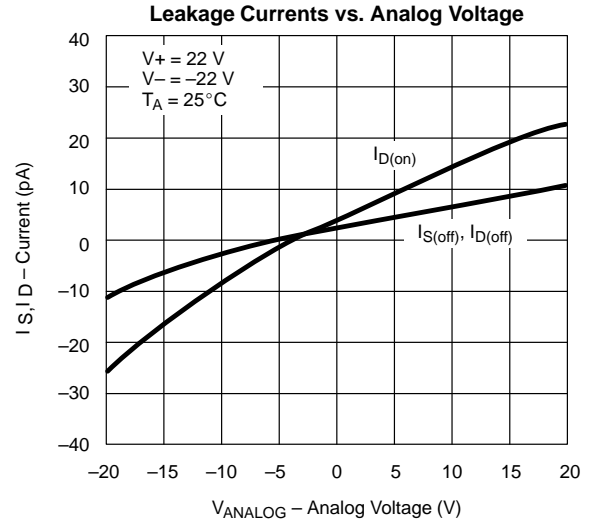
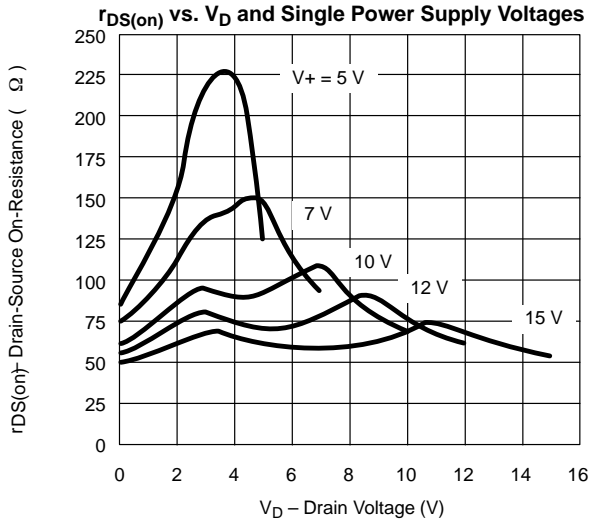
SPECIFICATIONS FOR SINGLE SUPPLY							
Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 12\text{ V}, V_- = 0\text{ V}$ $V_L = 5\text{ V}, V_{IN} = 2.4\text{ V}, 0.8\text{ V}^e$	Temp ^a	D Suffix -40 to 85°C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V_{ANALOG}		Full	0		12	V
Drain-Source On-Resistance	$r_{DS(on)}$	$V_D = 3\text{ V}, 8\text{ V}, I_S = 1\text{ mA}$	Room Full		90	160 200	Ω
Dynamic Characteristics							
Turn-On Time	t_{ON}	$V_S = 8\text{ V}$ See Figure 2	Room			300	ns
Turn-Off Time	t_{OFF}		Room			200	
Charge Injection	Q	$C_L = 1\text{ nF}, V_{gen} = 6\text{ V}, R_{gen} = 0\ \Omega$	Room		4		pC
Power Supply							
Positive Supply Current	I_+	$V_{IN} = 0\text{ or }5\text{ V}$	Room Full			10 50	μA
Negative Supply Current	I_-		Room Full	-10 -50			
Logic Supply Current	I_L		Room Full			10 50	
Power Supply Range for Continuous Operation	V_{OP}		Full	+4.5		+25	V

Notes:

- Room = 25°C, Full = as determined by the operating temperature suffix.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- Guaranteed by design, not subject to production test.
- V_{IN} = input voltage to perform proper function.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



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TEST CIRCUITS

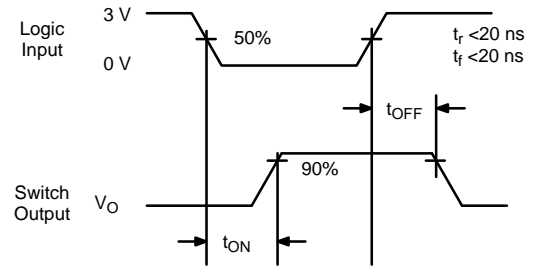
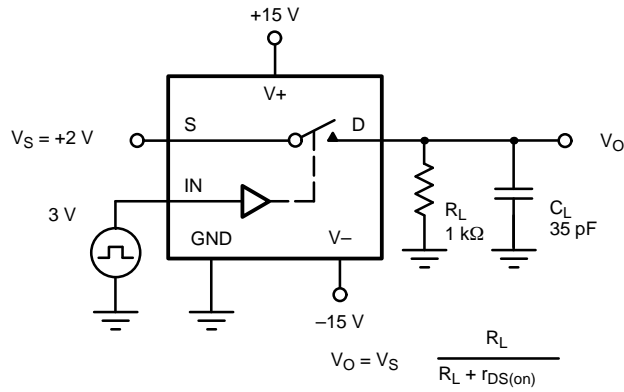


FIGURE 2. Switching Time

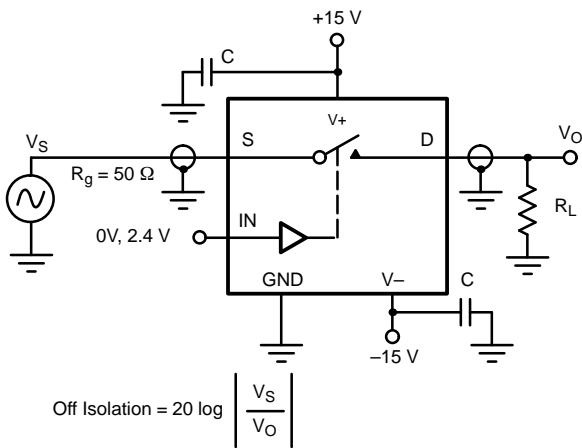


FIGURE 3. Off Isolation

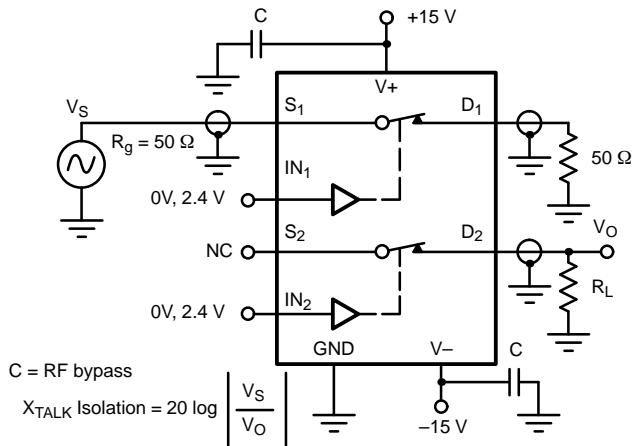
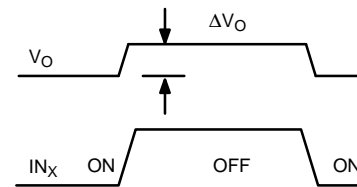
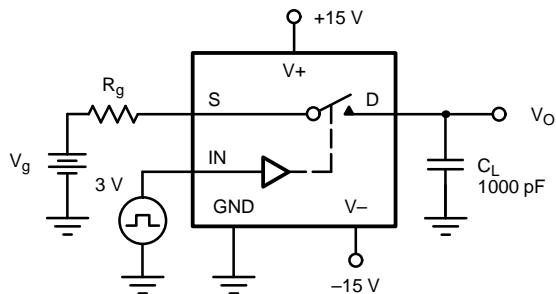
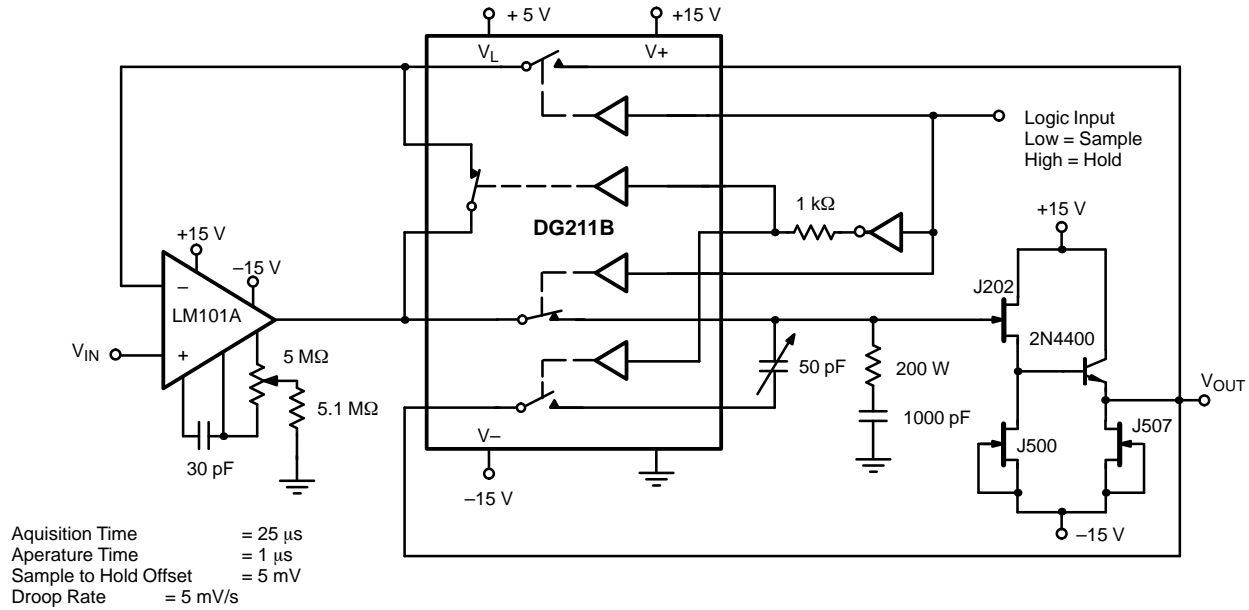
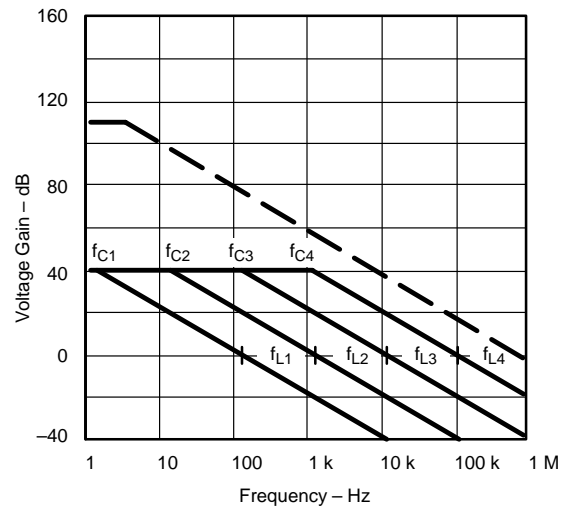
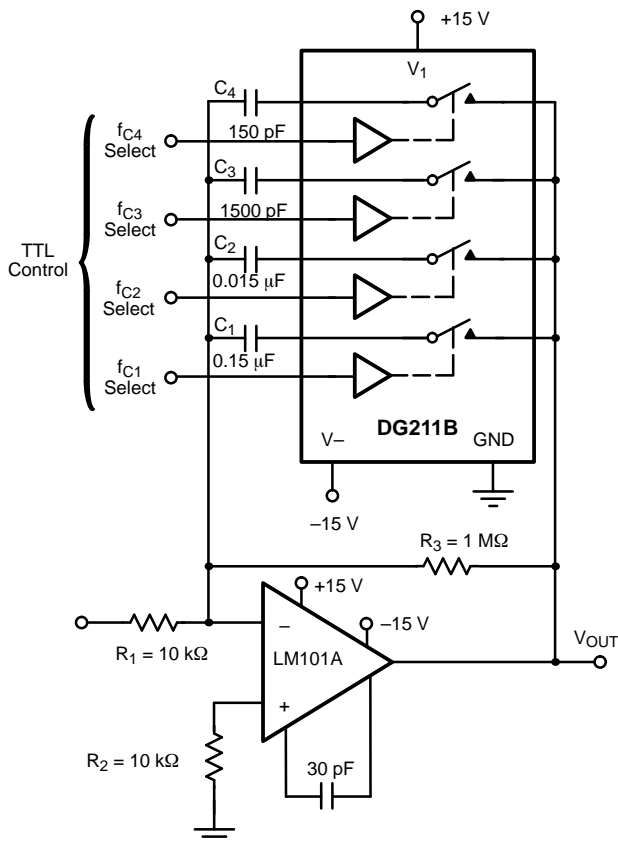


FIGURE 4. Channel-to-Channel Crosstalk



ΔV_O = measured voltage error due to charge injection
The charge injection in coulombs is $Q = C_L \times \Delta V_O$

FIGURE 5. Charge Injection

APPLICATIONS

FIGURE 6. Sample-and-Hold


$$A_L \text{ (Voltage Gain Below Break Frequency)} = \frac{R_3}{R_1} = 100 \text{ (40 dB)}$$

$$f_C \text{ (Break Frequency)} = \frac{1}{2\pi R_3 C_X}$$

$$f_L \text{ (Unity Gain Frequency)} = \frac{1}{2\pi R_1 C_X}$$

$$\text{Max Attenuation} = \frac{\Gamma_{DS(on)}}{10 \text{ k}\Omega} \approx -47 \text{ dB}$$

FIGURE 7. Active Low Pass Filter with Digitally Selected Break Frequency

APPLICATIONS

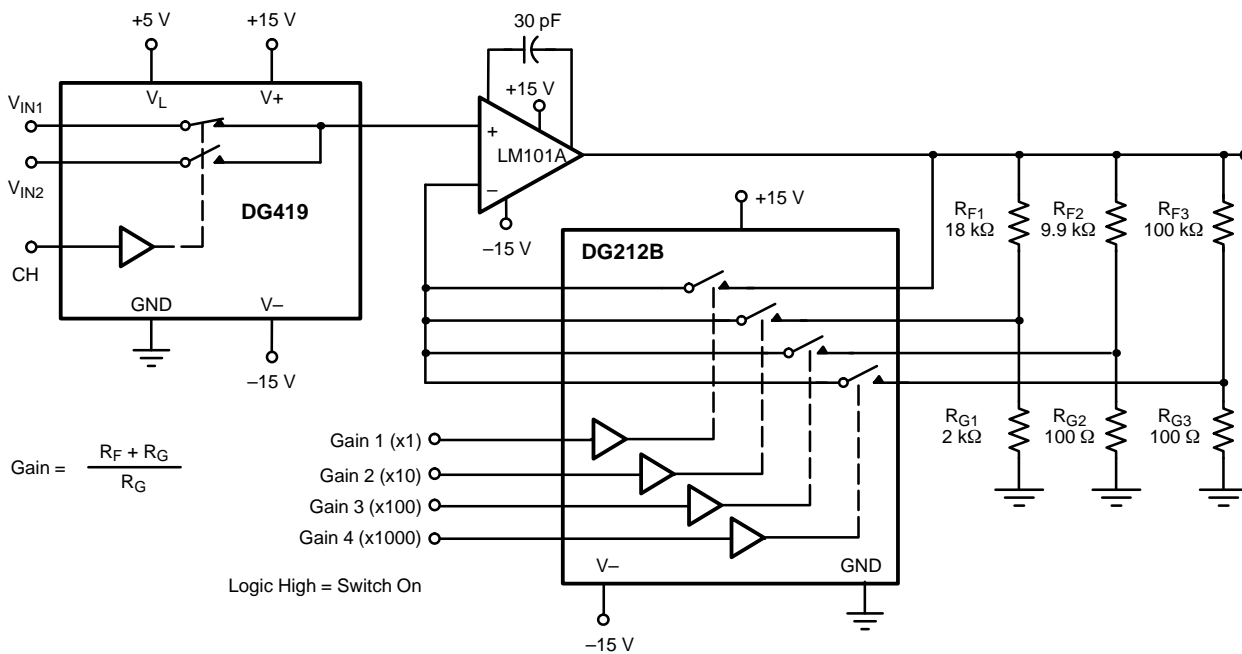


FIGURE 8. A Precision Amplifier with Digitally Programmable Input and Gains